
2SC4265

Silicon NPN Epitaxial

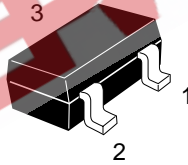
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Application

VHF RF amplifier, Local oscillator, Mixer

Outline

CMPAK



1. Emitter
2. Base
3. Collector

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Absolute Maximum Ratings (Ta = 25°C)

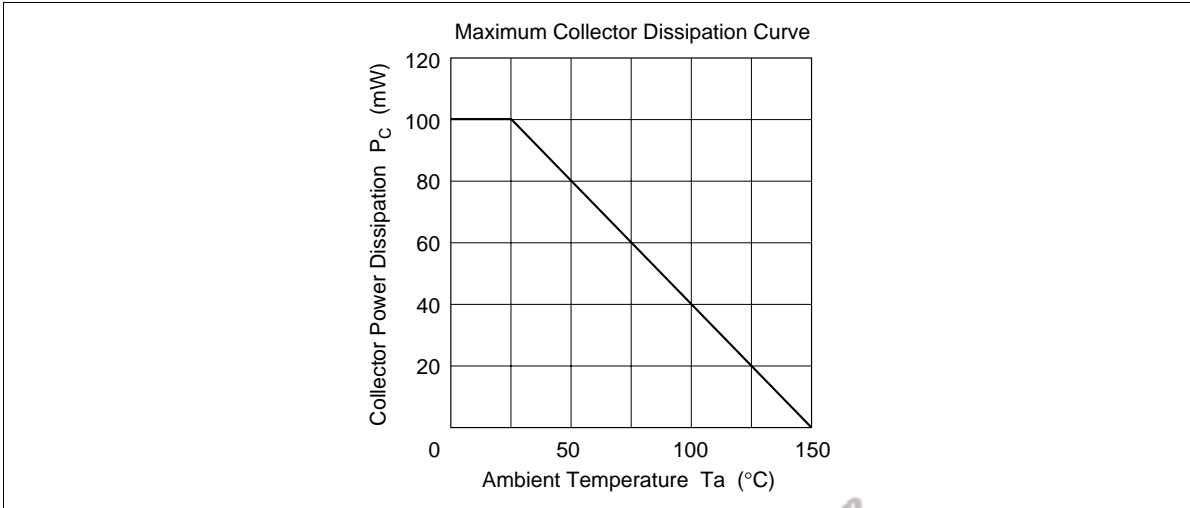
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CE} = 15 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 3 \text{ V}, I_C = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$
DC current transfer ratio	h_{FE}	40	—	—		$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$
Collector output capacitance	C_{ob}	—	—	1.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Gain bandwidth product	f_T	600	—	—	MHz	$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$

Note: Marking is "JC".

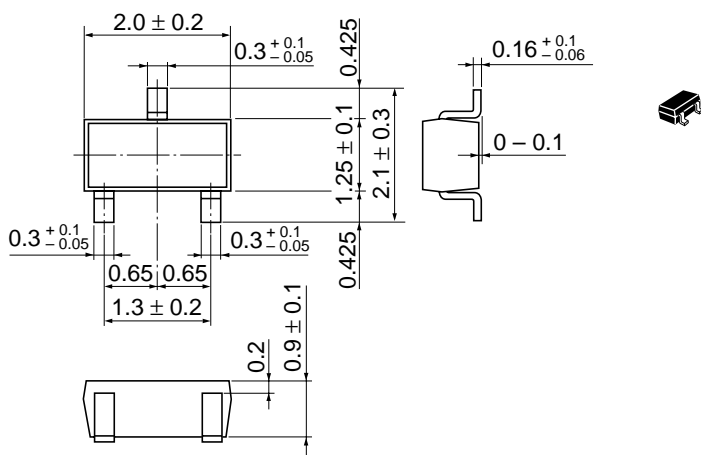
See characteristic curves of 2SC2735.



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Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.006 g

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